

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

SSM3K03FV

High Speed Switching Applications

Analog Switch Applications

- 2.5 V gate drive
- High input impedance
- Low gate threshold voltage: $V_{th} = 0.7\sim 1.3$ V
- Optimum for high-density mounting in small packages

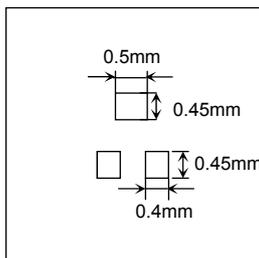
Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	20	V
Gate-source voltage	V_{GSS}	10	V
DC drain current	I_D	100	mA
Drain power dissipation (Ta = 25°C)	P_D (Note 1)	150	mW
Channel temperature	T_{ch}	150	°C
Storage temperature range	T_{stg}	-55~150	°C

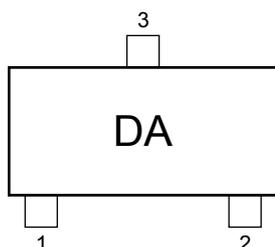
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

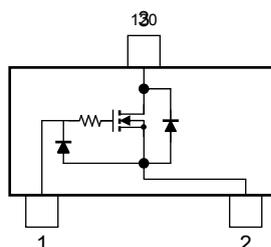
Note 1: Total rating, mounted on FR4 board



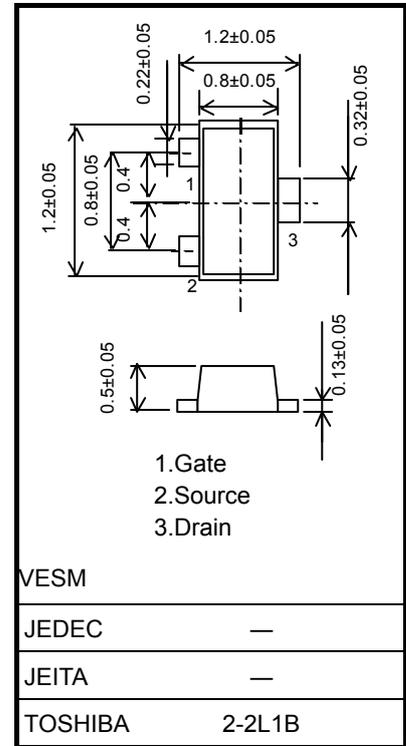
Marking



Equivalent Circuit



Unit: mm



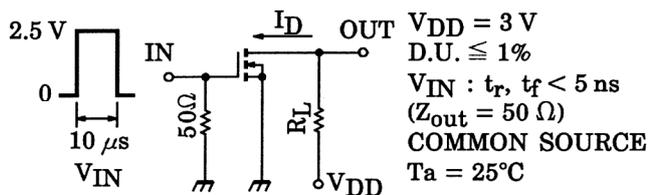
Weight: 1.5 mg (typ.)

Electrical Characteristics (Ta = 25°C)

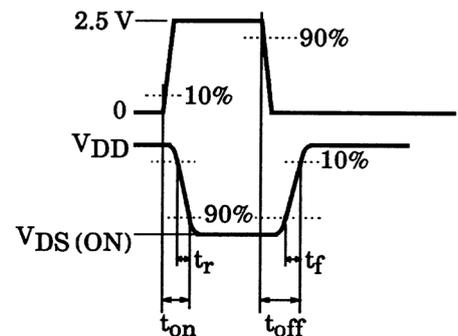
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit	
Gate leakage current	I_{GSS}	$V_{GS} = 10\text{ V}, V_{DS} = 0$	—	—	1	μA	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 100\ \mu\text{A}, V_{GS} = 0$	20	—	—	V	
Drain cut-off current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0$	—	—	1	μA	
Gate threshold voltage	V_{th}	$V_{DS} = 3\text{ V}, I_D = 0.1\text{ mA}$	0.7	—	1.3	V	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 3\text{ V}, I_D = 10\text{ mA}$	25	50	—	mS	
Drain-Source on-resistance	$R_{DS(ON)}$	$I_D = 10\text{ mA}, V_{GS} = 2.5\text{ V}$	—	4	12	Ω	
Input capacitance	C_{iss}	$V_{DS} = 3\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	11.0	—	pF	
Reverse transfer capacitance	C_{rss}	$V_{DS} = 3\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	3.3	—	pF	
Output capacitance	C_{oss}	$V_{DS} = 3\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	9.3	—	pF	
Switching time	Turn-on time	t_{on}	$V_{DD} = 3\text{ V}, I_D = 10\text{ mA}, V_{GS} = 0 \sim 2.5\text{ V}$	—	0.16	—	μs
	Turn-off time	t_{off}	$V_{DD} = 3\text{ V}, I_D = 10\text{ mA}, V_{GS} = 0 \sim 2.5\text{ V}$	—	0.19	—	

Switching Time Test Circuit

(a) Test circuit



(b) V_{IN}
 V_{GS}



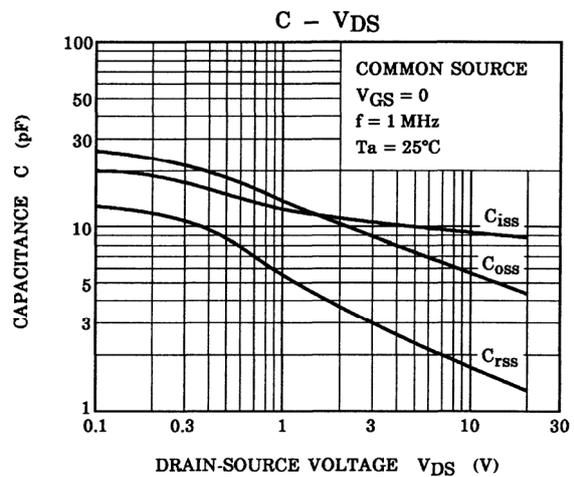
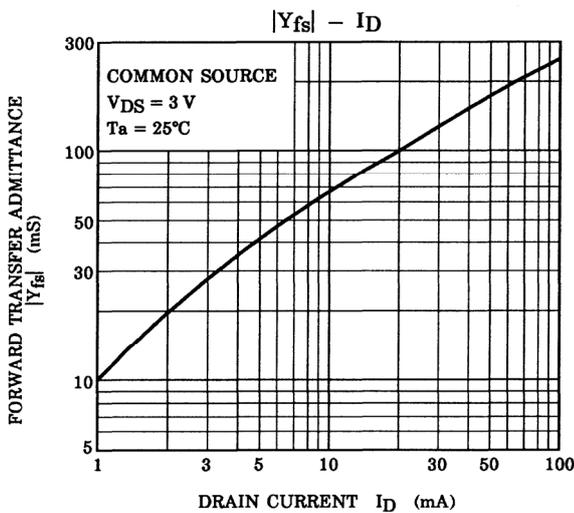
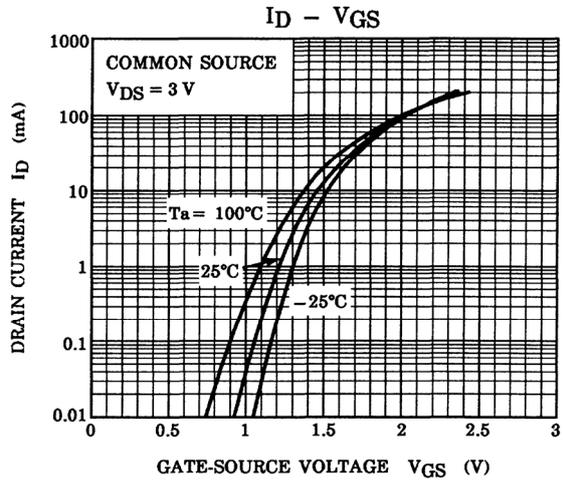
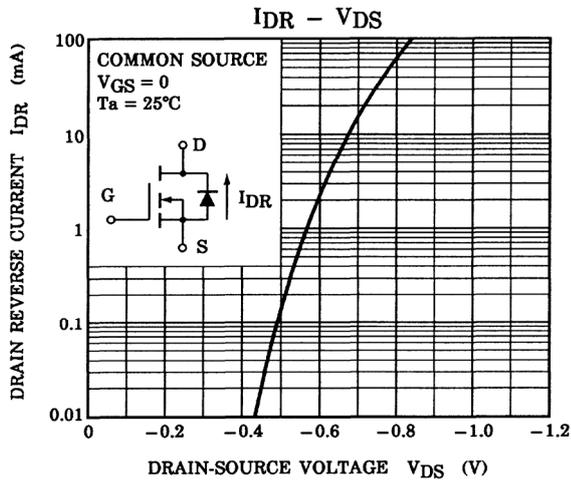
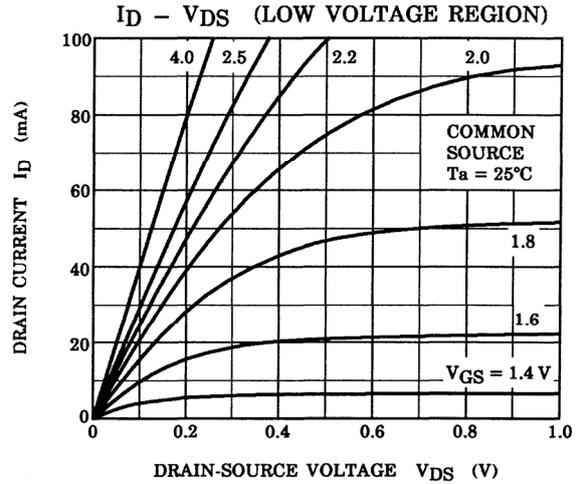
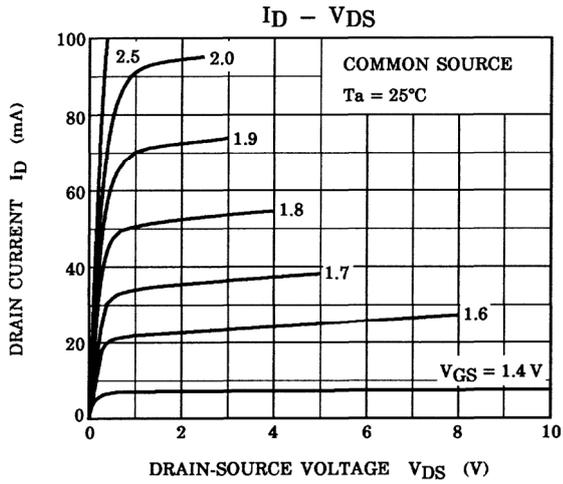
(c) V_{OUT}
 V_{DS}

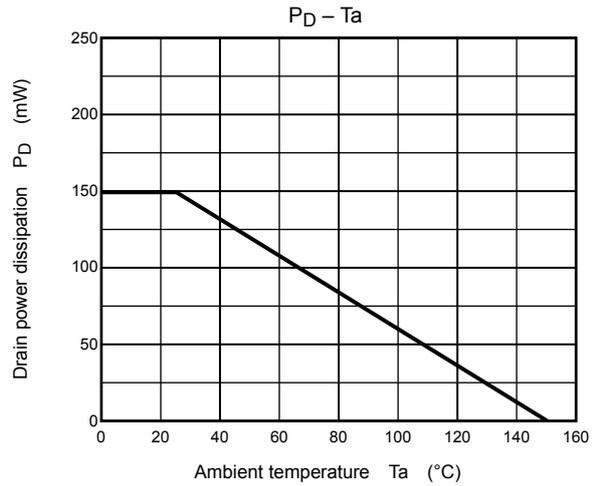
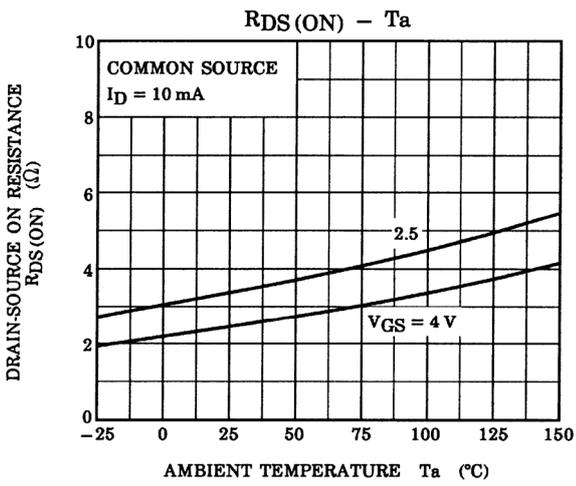
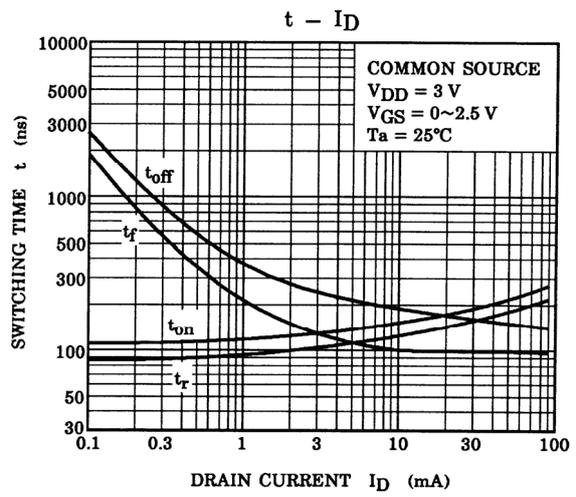
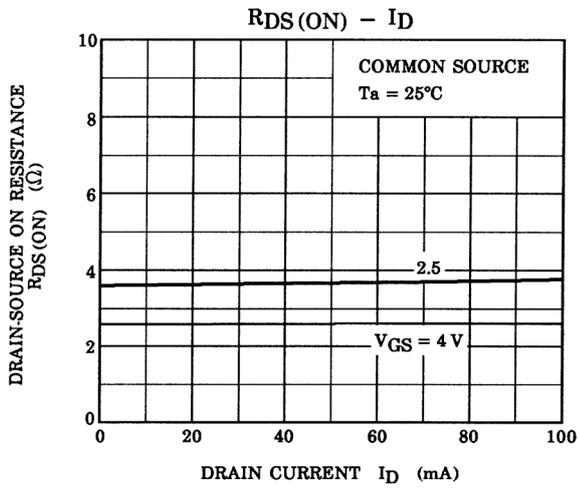
Precaution

V_{th} can be expressed as the voltage between gate and source when the low operating current value is $I_D = 100\ \mu\text{A}$ for this product. For normal switching operation, $V_{GS(ON)}$ requires a higher voltage than V_{th} and $V_{GS(OFF)}$ requires a lower voltage than V_{th} .

(The relationship can be established as follows: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$)

Take this into consideration when using the device.)





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20070701-EN GENERAL

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